

ABSTRACT OF THE DISCLOSURE

**ETCHING SOLUTION FOR SELECTIVELY REMOVING SILICON-GERMANIUM ALLOY
FROM A SILICON-GERMANIUM/ SILICON STACK DURING MANUFACTURE OF A
SEMICONDUCTOR DEVICE**

Described herein is an etching solution comprising water; oxidizer; water-miscible organic solvent; fluoride ion source; and optionally, surfactant. Such compositions are useful for the selective removal of silicon-germanium over poly silicon from a microelectronic device having such material(s) thereon during its manufacture.

(No drawing to be published)